ABSTRACT

SUBSTRATE PROCESSING APPARATUS, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE AND SUBSTRATE PROCESSING PROGRAM

Described herein is a technique capable of adjusting an inner pressure of a process chamber into a high vacuum state in a short time. According to one aspect of the technique, there is provided a substrate processing apparatus including: a process chamber; a pressure sensor; a first pipe; a first exhaust line comprising a first opening degree adjustment valve; a second pipe connected to the first exhaust line; a second exhaust line comprising a second opening degree adjustment valve; and a control unit. The control unit adjusts the opening degree of the second opening degree adjustment valve to bring the pressure in the process chamber to the processing pressure when the processing pressure is higher than the predetermined vacuum level, and the control unit adjusts the opening degree of the first opening degree adjustment valve to bring the pressure in the process chamber to the processing pressure when the processing pressure is lower than the predetermined vacuum level~~a substrate processing apparatus including: a process chamber; a main exhaust line including a first pipe, a first opening degree adjusting valve, an opening/closing valve and a pressure sensor; a bypass exhaust line including a second pipe and a second opening degree adjusting valve; and a controller configured to adjust an inner pressure of the process chamber by: (a) adjusting an opening degree of the second opening degree adjusting valve; (b) closing the second opening degree adjusting valve and opening the opening/closing valve and the first opening degree adjusting valve; and (c) closing the opening/closing valve and the first opening degree adjusting valve and adjusting the opening degree of the second opening degree adjusting valve~~.

Figure 1